

## isc Silicon PNP Power Transistor

2SB796

## DESCRIPTION

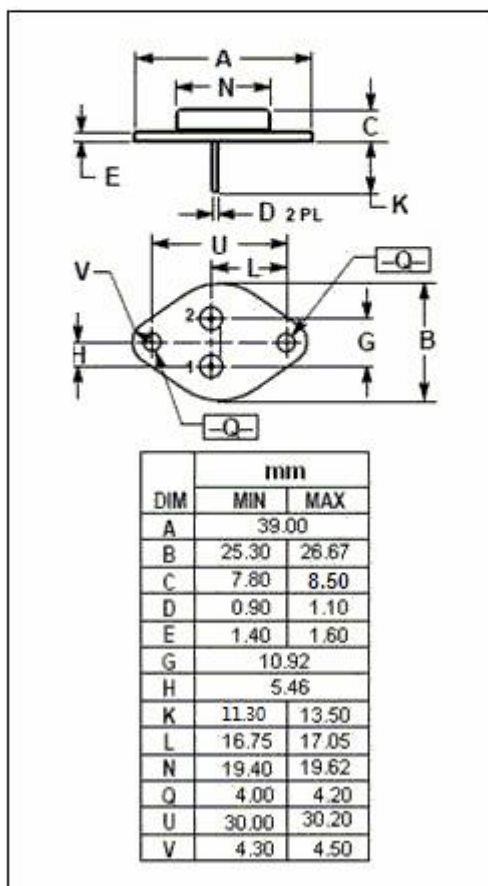
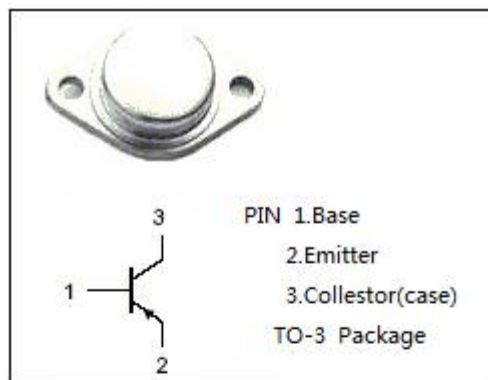
- Collector-Emitter Sustaining Voltage-  
:  $V_{CE(SUS)} = -200V(\text{Min})$
- Low Collector Saturation Voltage-  
:  $V_{CE(sat)} = -1.0V(\text{Max.}) @ I_C = -5A$
- Wide area of safe operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

- Designed for general-purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-200	V
$V_{CEO}$	Collector-Emitter Voltage	-200	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-10	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistor****2SB796****ELECTRICAL CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA; I <sub>B</sub> = 0	-200			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-5			V
V <sub>(BR)CBO</sub>	Collector-Base breakdown voltage	I <sub>C</sub> =-1mA; I <sub>E</sub> = 0	-200			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -200V; I <sub>E</sub> = 0			-100	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -200V; I <sub>B</sub> = 0			-100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -5V	40		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -5V	10			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> = -10V		15		MHz

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